

MAR 22 2004

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
51889/3 USAPPLICATION NO.
10/719,119

INFORMATION DISCLOSURE CITATION

Title: **DOUBLE-GATED TRANSISTOR CIRCUIT**

APPLICANT – Douglas R. Hackler, Sr. et al.

FILING DATE-
November 21, 2003

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PC	1	2002/0187610 A1	12/12/02	Furukawa et al.	438	283	06/12/01
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PC	16	5,436,506	07/25/95	Kim et al.	257	347	10/12/93

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PC	17	5,349,228	09/20/94	Neudeck et al.	257	365	12/07/93
PC	18	5,273,921	12/28/93	Neudeck et al.	437	41	12/27/91
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		DOCUMENT NUMBER	PUBLICA- TION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	20							
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	59	Solomon et al., "Two Gates Are Better Than One," IEEE Circuits & Devices Magazine, January 2003, pgs. 48-63.
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PC	74	Ducroquet et al., "Full CMP Integration of CVD TiN Damascene Sub-0.1- μ m Metal Gate Devices For ULSI Applications," IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001, pgs. 1816-1821.
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PC	90	Yagishita et al., "High Performance Metal Gate MOSFETs Fabricated by CMP for 0.1 μ m Regime," Microelectronics Engineering Laboratory, Toshiba Corporation, 8, Shinsugita-cho, Isogo-ku, Yokohama 235-8522, Japan, pgs. 29.3.1-29.3.4.
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pc	A1	2003/0058001	03/27/03	Boerstler et al.	326	113	09/27/01	
	A2	2002/0180486	12/05/02	Yamashita et al.	326	113	06/25/02	
	A3	2002/0084803	07/04/02	Mathew et al.	326	113	12/29/00	
	A4	2002/0081808	06/27/02	Forbes	438	283	01/25/02	
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	A7	6,433,609	08/13/02	Voldman	327	313	11/19/01	
	A8	6,420,905	07/16/02	Davis et al.	326	113	09/07/00	
	A9	6,404,237	06/11/02	Mathew et al.	326	113	12/29/00	
	A10	6,376,317	04/23/02	Forbes et al.	438	283	06/28/00	
pc	A11	6,188,243	02/13/01	Liu et al.	326	81	06/09/99	
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PC	A12	6,104,068	08/15/00	Forbes	257	365	09/01/98
R	A13	6,097,221	08/01/00	Sako	326	113	12/10/96
PC	A14	6072,354	06/06/00	Tachibana et al.	327	390	09/29/97
R	A15	4,468,574	08/28/84	Engeler et al.	307	451	05/03/82
PC	A16	4,300,064	11/10/81	Eden	307	446	02/12/79

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